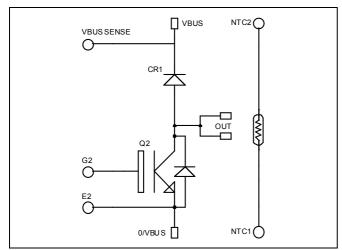


Boost chopper Fast Trench + Field Stop IGBT3 Power Module

$$V_{CES} = 1200V$$

 $I_{C} = 75A$ @ $Tc = 80$ °C

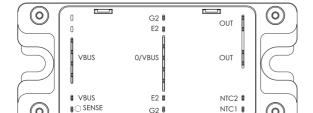


Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Fast Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
 - Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
 - High level of integration
- Internal thermistor for temperature monitoring



Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- **RoHS Compliant**

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_{C}	Continuous Collector Current	$T_C = 25$ °C	110	
1 _C	Continuous Conector Current	$T_C = 80$ °C	75	A
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	175	
$ m V_{GE}$	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	357	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	150A @ 1150V	

NTC1 (

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μA
V _{CE(sat)}	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	1.4	1.7	2.1	V
		$I_C = 75A$	$T_{j} = 125^{\circ}C$		2.0		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$		5.0		6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE}$	$V_{GE} = 20V$, $V_{CE} = 0V$			400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			5340		
C_{oes}	Output Capacitance	$V_{CE} = 25V$	$V_{CE} = 25V$ f = 1MHz		280		pF
C_{res}	Reverse Transfer Capacitance	f = 1MHz			240		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			260		
T_{r}	Rise Time	$V_{GE} = \pm 15V$			30		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 75A$			420		
T_{f}	Fall Time	$R_G = 4.7\Omega$		70		ı	
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ning (125°C)		285		
T_{r}	Rise Time	$V_{GE} = \pm 15V$			50		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 75A$			520		ns
$T_{\rm f}$	Fall Time	$R_G = 4.7\Omega$			90		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125$ °C		7		ma I
E_{off}	Turn-off Switching Energy	$I_C = 75A$ $R_G = 4.7\Omega$	$T_j = 125$ °C		8.1		mJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_{R}=1200V$	$T_j = 25$ °C			250	μA
KWI		K	$T_j = 125$ °C			500	
I_F	DC Forward Current		Tc = 80°C		75		Α
V_{F}	Diode Forward Voltage	$I_F = 75A$	$T_i = 25^{\circ}C$		1.5	2.0	V
v _F	Diode Polward Voltage	$I_{\rm F} = 75$ A	$T_{i} = 125^{\circ}C$		1.4		V
t_{rr}	Reverse Recovery Time	$T_i = 125^{\circ}C$	$T_j = 25$ °C		150		ns
·rr	Reverse Recovery Time		$T_j = 125$ °C		250		113
0	Reverse Recovery Charge	$I_F = 75A$ $V_R = 600V$	$T_j = 25$ °C		7		μС
Q_{rr}	Reverse Recovery Charge	$di/dt = 2000 \text{ A}/\mu\text{s}$	$T_{j} = 125^{\circ}C$		13.5] μC
E _r	Reverse Recovery Energy		$T_j = 25$ °C		3.7		mJ
\mathbf{L}_{r}	Reverse Recovery Ellergy		$T_j = 125$ °C		7.2		1113



 $Temperature\ sensor\ NTC\ (see\ application\ note\ APT0406\ on\ www.microsemi.com\ for\ more\ information).$

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

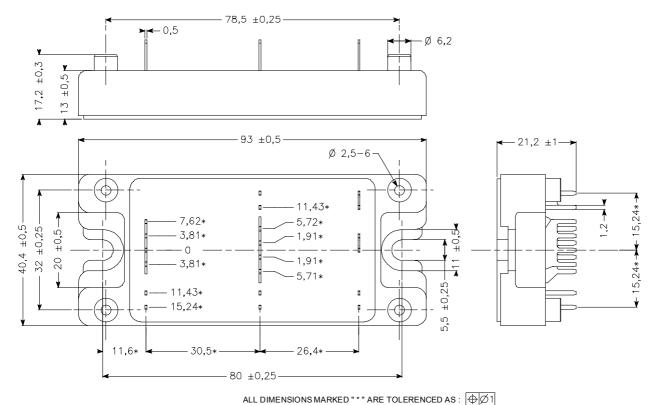
$$R_{T} = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_{T}: \text{ Thermistor value at T}$$

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.35	°C/W
TthJC	Diode Diode	Diode			0.48	C/ \\	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t	=1 min, 50/60Hz		4000			V
T_{J}	Operating junction temperature range		-40		150		
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		125	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight				160	g	

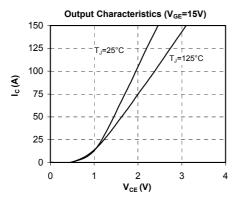
SP4 Package outline (dimensions in mm)

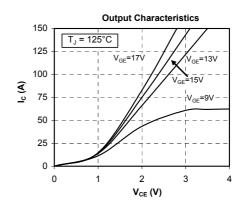


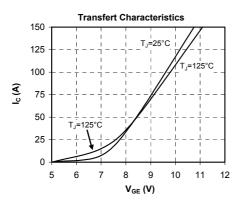
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

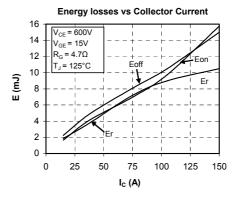


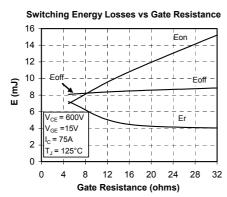
Typical Performance Curve

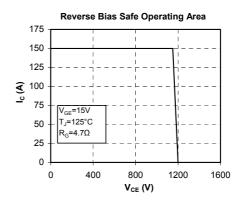


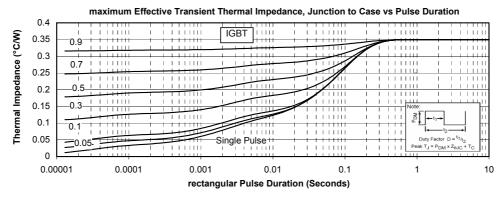




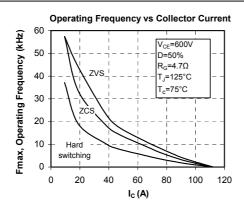


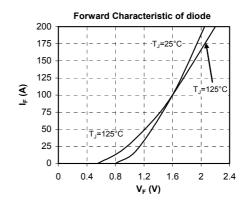


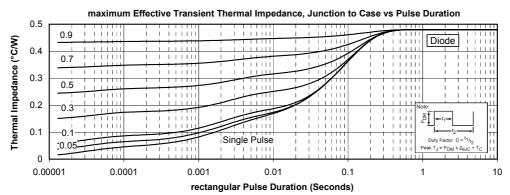












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